

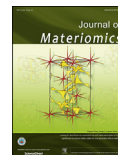


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Graphical Abstracts

## Review Articles

### Multiferroic heterostructures and tunneling junctions

Weichuan Huang<sup>a</sup>, Shengwei Yang<sup>a</sup>, Xiaoguang Li<sup>a,b,c,\*</sup>

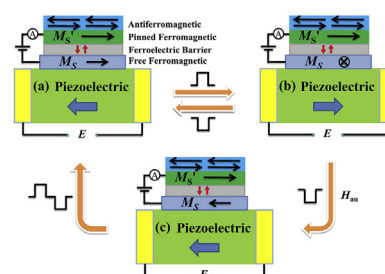
<sup>a</sup>Hefei National Laboratory for Physical Sciences at Microscale, Department of Physics, University of Science and Technology of China, Hefei 230026, China

<sup>b</sup>Collaborative Innovation Center of Advanced Microstructures, Nanjing University, Nanjing 210093, China

<sup>c</sup>Key Laboratory of Materials Physics, Institute of Solid State Physics, CAS, Hefei 230031, China

We review the recent advances as well as the potential applications of strain- and charge-mediated magnetoelectric coupling effects on the magnetic and electronic transport properties in multiferroic heterostructures and multiferroic tunnel junctions.

*J Materiomics 2015, 1, 263–284*



### An overview of materials issues in resistive random access memory

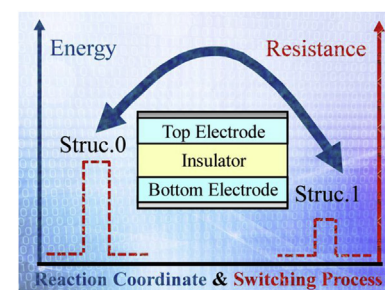
Linggang Zhu<sup>a,b</sup>, Jian Zhou<sup>a</sup>, Zhonglu Guo<sup>b</sup>, Zhimei Sun<sup>a,b,\*</sup>

<sup>a</sup>School of Materials Science and Engineering, Beihang University, Beijing 100191, China

<sup>b</sup>Center for Integrated Computational Materials Engineering, International Research Institute for Multidisciplinary Science, Beihang University, Beijing 100191, China

Some general rules of material selection for resistive random access memory (RRAM) are proposed. Mechanisms of resistance switch in RRAM are reviewed. Computational material science will play an important role in the design of RRAM.

*J Materiomics 2015, 1, 285–295*



## Helices in micro-world: Materials, properties, and applications

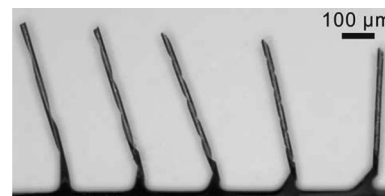
Gaoshan Huang<sup>a,b</sup>, Yongfeng Mei<sup>a,\*</sup>

<sup>a</sup>Department of Materials Science, Fudan University, Shanghai 200433, People's Republic of China

<sup>b</sup>Key Laboratory of Inorganic Coating Materials, Chinese Academy of Sciences, Shanghai 200050, People's Republic of China

This overview reviews recent progresses in micro-helices related researches. The micro-helices can be produced by numerous approaches, either “top-down” or “bottom-up”. Micro-helices have unique properties in mechanics, electrics, magnetics, optics, etc. Micro-helices have great potential in micro-electro-mechanical system and lab-on-a-chip.

*J Materiomics* 2015, 1, 296–306



## Original Articles

### Band and scattering tuning for high performance thermoelectric $\text{Sn}_{1-x}\text{Mn}_x\text{Te}$ alloys

Wen Li<sup>a</sup>, Zhiwei Chen<sup>a</sup>, Siqi Lin<sup>a</sup>, Yunjie Chang<sup>b</sup>, Binghui Ge<sup>b</sup>, Yue Chen<sup>c</sup>, Yanzhong Pei<sup>a,\*</sup>

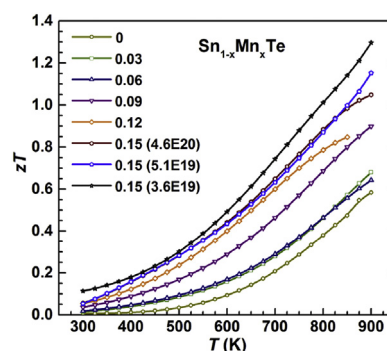
<sup>a</sup>Key Laboratory of Advanced Civil Engineering Materials of Ministry of Education, School of Materials Science and Engineering, Tongji Univ., 4800 Caoan Rd., Shanghai 201804, China

<sup>b</sup>Beijing National Laboratory for Condensed Matter Physics, Institute of Physics, Chinese Academy of Science, Beijing 100190, China

<sup>c</sup>Department of Mechanical Engineering, The University of Hong Kong, Pokfulam Road, Hong Kong SAR, China

According to our previous experiences on successful manipulation of band structure by alloying, this work is motivated by a heavily alloying strategy for aligning the bands from the well-separated ones in pristine SnTe. The resulting well-aligned conducting channels (bands) for charge carriers and high-concentration blocking centers for heat carriers (phonons) propagation, lead to a record thermoelectric figure of merit,  $zT = 1.3$  in SnTe alloys. Most importantly, the obtained high performance does not rely on any other independent strategies than alloying for even lower thermal conductivity, enabling a bright future for a further improvement.

*J Materiomics* 2015, 1, 307–315



### Gas induced reduction synthesis of $\text{Sb}_2\text{Te}_3$ and $\text{Bi}_{0.5}\text{Sb}_{1.5}\text{Te}_3$ nanosheets and their evolvement mechanism

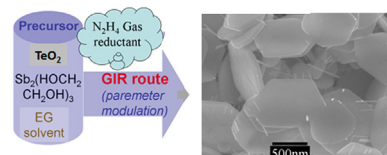
Xin Wang<sup>a</sup>, Kefeng Cai<sup>a,\*</sup>, Baijun An<sup>a</sup>, Shirley Shen<sup>b,\*\*</sup>

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<sup>b</sup>CSIRO Manufacturing, New Horizon Building, Clayton, VIC 3168, Australia

Binary  $\text{Sb}_2\text{Te}_3$  and ternary  $\text{Bi}_{0.5}\text{Sb}_{1.5}\text{Te}_3$  hexagonal nanopellets were synthesized. The nanosheets were synthesized by a gas-induced reduction method. The formation mechanism of the nanopellets was proposed.

*J Materiomics* 2015, 1, 316–324



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